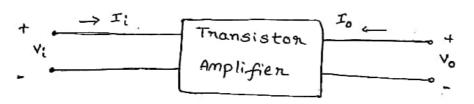
#### BJT AMPLIFIERS

# H-Panameter Representation of a Transiston

A transiston can be treated as a two-port Network



Hene Ii = Input connent to the Amplifien

Vi = Input Voitage to the Amplifier

To = output connent of the Amplifier

Vo = output voitage of the Amplifien

Transistor is a current operated device.

Here input voltage Vi and output corrent to are the dependent variables.

Input current Ii and output voitage vo are Independent Vaniables.

$$V_{l} = f_{l} \left( \Xi_{l}, V_{o} \right).$$

This can be written in the equation form as follows

The above equation can also be written using alphabetic notations

$$V_{l} = h_{l} I_{l} + h_{n} V_{0}$$

$$T_{0} = h_{f} I_{l} + h_{0} V_{0}$$

#### Definitions of h- parameter:

The parameters in the above equation are defined as follows

$$h_{ii} = h_i = \frac{V_i}{T_i}$$
 = Input Mesistance with output  $V_0 = 0$  Short circuited.

$$h_{12} = h_n = \frac{V_i}{I_0} \Big|_{I_i=0}$$
 = Revense voitage transfer ratio with input open cincuited.

$$h_{21} = h_f = \frac{T_0}{T_i} \Big|_{V_0=0}$$
 = short circuit x current gain with output short circuited.

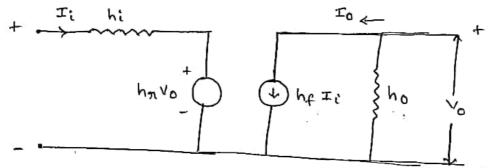
$$h_{22} = h_0 = \frac{I_0}{V_0} \Big|_{I_1=0} = \begin{array}{c} \text{output Admittance with input} \\ \text{open circuited.} \end{array}$$

#### BJT H-panameter model:

Based on the definition of hybrid parameters the mathematical model for two port networks known as h-parameter model (Hybrid Parameter model) can be developed.

The two equations of a transistor is given by  $V_i = h_i \, T_i \, + \, h_n \, V_0$   $T_0 = h_f \, T_i \, + \, h_0 \, V_0$ 

Based on above two equations the equivalent circuit on Hybrid Model for transistor can be drawn.

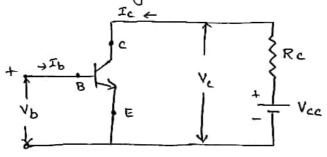


Advantages (on) Benifits of h- panameters

- 1) Real numbers at audio frequencies
- 2) Easy to measone
- 3) can be obtained from the transistor static characteristic curves.
- 4) convinient to use in circuit analysis and design.
- 5) Easily convertable from one configuration to other
- 6) most of the transistor manufacturers sepecify the h-parameters.

H panameter model for CE configuration

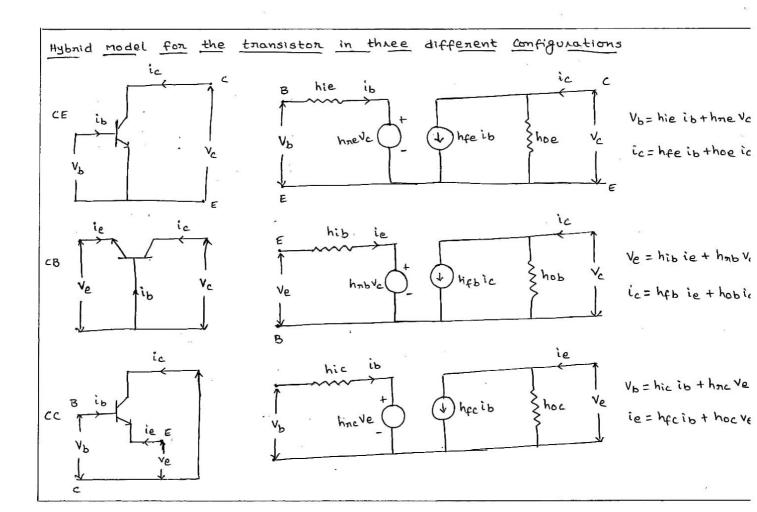
Let us consider the common emitter configuration shown in figure below. The Variables Tb, Tc, Vb and Vc represent total instantaneous cornents and Voltages,



Rc Fig: simple common emitten

Vcc configuration

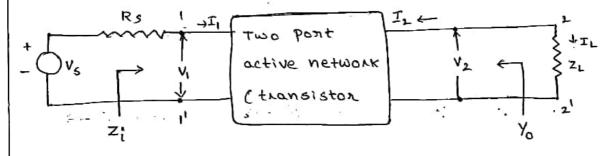
Here Ib - Input corrent Vb - Input Voltage Ic - output current Vc - output Voitage h- parameter model for common emitter configuration shown in figure below. Vb = hie Ib + hne Vc Ic = hee Ib + hoe Ve  $hie = \frac{\Delta V_B}{\Delta I_B} \bigg|_{V_c = constant} = \frac{V_b}{I_b} \bigg|_{V_c = constant}$ where hne =  $\frac{\Delta V_B}{\Delta V_C}$  |  $I_B = Constant$  =  $\frac{V_b}{V_c}$  |  $I_b = Constant$ here =  $\frac{\Delta T_c}{\Delta T_B}$  |  $V_c = constant$  =  $\frac{i_c}{i_b}$  |  $V_c = constant$  $h_{OQ} = \frac{\Delta I_C}{\Delta V_C} \Big|_{IB = Constant} = \frac{i_C}{V_C} \Big|_{I_b = Constant}$ 



Typical h-parameter values for a transistor				
Parameter	CE	cc	cВ	
hi	11002	11001	22 V	
hn	2.5 × 10-4	1	3 x 10 4	
her-	50	-51	-0198	
ho	25 MA/V	25 MA/V	0.49 MA/V	

Analysis of a transistor amplifier circuit using h-parameter model.

A transistor amplifier can be constructed by connecting an external load and signal source as indicated in figure below and biasing the transistor properly.



The hybrid parameter model for above network is shown in figure below.

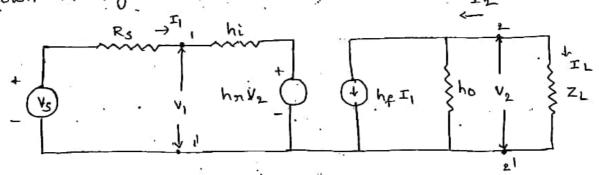


Fig: Transiston hybrid parameter model.

Cunnent Gain (on) Cunnent Amplification A:

For a transistor amplifier the current gain Az is defined as the natio of output current to input current.

$$A_{I} = \frac{I_{L}}{I_{I}} = -\frac{I_{2}}{I_{I}}$$

From the circuit  $I_2 = h_f I_1 + h_0 V_2 \longrightarrow 0$   $V_2 = I_L Z_L = -I_2 Z_L \longrightarrow (2)$ 

Sub 2 in 0  $T_2 = hf I_1 - I_2 Z_L h_0$   $I_2 + I_2 Z_L h_0 = hf I_1$ 

$$I_2(1+Z_Lh_0) = hf I_1 \Rightarrow \frac{I_2}{I_1} = \frac{hf}{1+Z_Lh_0}$$

$$A_{I} = \frac{-I_{2}}{I_{1}} = \frac{-hf}{1+Z_{L}ho}$$

AI

2) Input Impedance zi

In the circuit  $R_s$  is the signal source resistance the impedance seen when looking in to the amplifien terminals (1,1') is the amplifier input impedance  $z_i$ 

$$z_i = \frac{v_i}{T_i}$$

From figure V1 = hi I1 + hn V2

So 
$$Z_1 = \frac{h_1 T_1 + h_1 N_2}{T_1} = h_1 + h_1 \frac{N_L}{T_1} \rightarrow \mathbb{O}$$
 $V_2 = -T_2 Z_L = A_1 T_1 Z_L$ 
 $V_2 = -I_2 Z_L = A_1 T_1 Z_L$ 
 $V_3 = h_1 + h_1 \frac{A_1 T_1 Z_L}{T_1}$ 
 $V_4 = \frac{-T_2}{T_1}$ 
 $V_5 = h_1 + h_1 A_1 T_2 Z_L$ 
 $V_6 = h_1 - h_1 h_1 \frac{h_1}{1 + h_0 Z_L}$ 
 $V_7 = h_1 - \frac{h_1 h_1}{1 + h_0 Z_L}$ 
 $V_8 = h_1 - \frac{h_1 h_1}{N_1 + h_0}$ 
 $V_8 = \frac{N_1 - h_1 h_1}{N_1 + h_0}$ 
 $V_8 = \frac{N_1 - h_1 h_1}{N_1 + h_0}$ 
 $V_8 = \frac{N_1 - h_1 h_1}{N_1 + h_0}$ 
 $V_8 = \frac{N_1 + h_1}{N_1 + h_0}$ 
 $V_9 =$ 

CB

CC

$$V_0 = \frac{\Gamma_2}{V_2}$$
 with  $V_S = 0$  and  $R_L = \infty$ 

from the circuit 
$$I_2 = h_f I_1 + h_0 Y_2$$

Dividing by 
$$V_2$$
,  $\frac{T_2}{V_2} = h_f \frac{T_1}{V_2} + h_0 \longrightarrow 0$ 

with Vs = 0, by KVL in input cincuit

Hence 
$$\frac{T_1}{V_2} = \frac{h_n}{R_s + h_i}$$

NOW Eq (1) 
$$\Rightarrow \frac{T_2}{V_2} = \frac{-hf hn}{R_5 + hi} + ho$$

$$\Rightarrow y_0 = h_0 - \frac{h_f h_n}{R_s + h_i}$$

CE

CB

د د

$$A_{VS} = \frac{V_2}{V_S} = \frac{V_2}{V_1} \frac{V_1}{V_S} \Rightarrow A_{VS} = A_V \frac{V_1}{V_S}$$

$$V_1 = \frac{V_s z_i}{V_s + z_i} \implies \frac{V_1}{V_s} = \frac{z_i}{R_s + z_i}$$

$$A_{VS} = \frac{A_{I} R_{L}}{z_{1}^{2}} \times \frac{z_{L}}{R_{S} + z_{L}} = \frac{A_{I} R_{L}}{R_{S} + z_{L}^{2}}$$

of 
$$R_s = 0$$
 then  $Av_s = \frac{AIRL}{Z_i} = Av$ .

6) coment Amplification (AIS)

$$A_{IS} = \frac{-I_2}{I_S} = \frac{-I_2}{I_1} \cdot \frac{I_1}{I_S} = A_I \cdot \frac{I_1}{I_S}$$

The modified input cincuit using Nonton's equivalent cincuit for the sounce for the calculation of AIS

$$A_{IS} = A_{I} \frac{R_{S}}{R_{S} + Z_{I}}$$

$$\left( z_{L} = R_{L} \right)$$

⇒ In cc configuration Connent gain AI = -Input Impedance zi = hic - hfc hnc YL + hoc Voitage gain Av = AIZL output Admittance Yo = hoc - hic + Rs Convension formulae for hybrid parameters > CC CB hib = hie 1+hfe hic = hie hnb = hie hoe - hne hnc = 1 hfb = -hfe hfc = - (i+ hfe) hob = hoe hoc - hoe 1) characteristics of common emitter Amplifier 1) corrent gain AI is high for RL < 10 Kr 2) the voltage gain is high for normal values of Load nesistance RL 3) The input mesistance Ri is medium

4) The output resistance Ro is moderately high

# Applications of common emitter amplifier:

- 1. of the three configurations ce amplifier alone is capable of providing both voltage gain and current gain.
- 2. The output nesistance Ro and input nesistance Ri are moderately high
- 3. CE amplifien is widely used for Amplification purpose characteristics of common Base Amplifien:
- 1. Current gain is less than unity and its magnitude decreases with the increase of load resistance RL
- 2. Voitage gain Av is high for normal values of RL
- 3. The input nesistance Ri is the lowest of all the three configurations.
- 4. The output resistance Ro is the highest of all the three configurations.

# Applications of common base Amplifier

The CB Amplifien is not commonly used for Amplification purpose. It is used for

- 1) Matching a very low impedance source.
- 2) As a non inventing amplifien with voltage gain exceeding unity
- 3) For driving a high impedance load
- 4) As a constant current sounce.
- 3) characteristics of common collector Amplifier

  1 For low value of RL (<10KN) The cument gain A= 15

  high and almost equal to that of a CE amplifier

- 2. The voltage gain Av is less than unity.
- 3. The input nesistance is the highest of all the three configurations.
- 4 The output Mesistance is the lowest of all the three configurations.

### Applications of common collector Amplifier:

1. The cc Amplifier is widely used as a buffer stage between a high impedance source and low impedance load. (cc Amplifier is called emitter follower)

companison of Transiston Amplifier Configurations.

the characteristics of three configurations are summarized in table below. Here the quantities  $A_{\pm}$ ,  $A_{V}$ ,  $R_{i}$ ,  $R_{o}$  and  $A_{p}$  (Power gain) are calculated for  $R_{L}=R_{S}=3k$ .

quantity	CB	CC	CE .
Ar	0.98	47.5	-46.5
$A_{V}$	131	0.989	-131
Ap	128.38	46.98	6091.5
R(	રીશ.6 ∧	144 KJ	1065 N
Ro	1.72MA	80.5A	45.5 KJ

Simplified CE Hybrid model (02) Approximate CE Hybrid model (Approximate Analysis):

As the h parameters themselves vary widely for the same type of transistor. It is justified to make approximations and simplify the expressions for AI, AV, Ap, Ri and Ro.

The behaviour of the transiston circuit can be obtained by using the simplified hybrid model. The h-parameter equivalent circuit of the transistor in the CE configuration is shown in figure below.

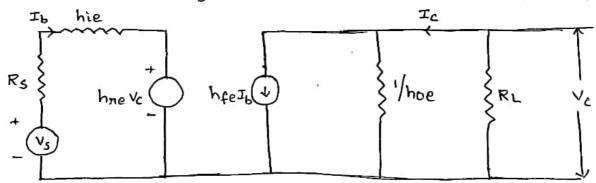


Fig: Exact CE Hybrid Model.

Here I is in parallel with RL

The panallel combination of two unequal impedances is approximately equal to the lower value le RL. Hence if  $\frac{1}{hoe} >> RL$ , then the term hoe may be neglected provided that hoe RL << 1

If hoe is omitted, the collector current Ic is given by  $I_C = hee I_b$ .

generated in the emitter circuit is

hne  $|V_c|$  = hne  $I_c$   $R_L$  = hne hfe  $I_b$   $R_L$  Since hne hfe  $\approx$  0.01, this voltage may be heglected in companison with the voltage drop across hie. ie hie  $I_b$  provided that  $R_L$  is not too large. ie  $f_b$  the load  $f_b$   $f_b$ 

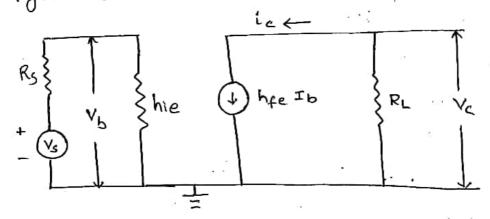


Fig: Approximate CE Hybrid model.

1) CULLENT Gain (AI):

The current gain for CE configuration is

2) Input Impedance (Z1):

By exact analysis 
$$Z_i = R_i = \frac{V_i}{I_i}$$

$$V_{1} = hie I_{1} + hne V_{2}$$

$$Z_{1}^{2} = \frac{hie I_{1} + hne V_{2}}{I_{1}} = hie + hne \frac{V_{2}}{I_{1}}$$

$$V_{2} = -I_{2}Z_{L} = -I_{2}R_{L} = A_{1}I_{1}R_{L} \qquad \left( \begin{array}{c} A_{1} = \frac{-I_{2}}{I_{1}} \\ A_{2} = \frac{-I_{2}}{I_{1}} \end{array} \right)$$

$$\Rightarrow Z_{1}^{2} = hie + hne \frac{A_{1}I_{1}R_{L}}{I_{1}} \qquad \left( \begin{array}{c} V_{2} = A_{1}I_{1}R_{L} \\ I = A_{2}I_{1}R_{L} \end{array} \right)$$

$$R_{1}^{2} = hie \left( \begin{array}{c} I + \frac{hne A_{1}R_{L}}{hie} \\ hie \end{array} \right)$$

$$R_{1}^{2} = hie \left( \begin{array}{c} I + \frac{hne A_{1}R_{L}}{hie} \\ hie \end{array} \right)$$

$$Vsing the typical values for the h-parameters$$

$$\frac{hne hee}{hie hoe} \cong 0.5$$

$$\Rightarrow R_{1}^{2} = hie \left( \begin{array}{c} I + \frac{0.5 A_{1}R_{L}}{hoe} \\ hee} \\ hee know that A_{2} = \frac{-hee}{I + hoe} \\ I + hoe R_{L} \\ \end{pmatrix}$$

$$\Rightarrow R_{1}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ hee} \\ hee \\ R_{1}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ hee} \\ hee \\ R_{2}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ hee} \\ R_{3}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ hee} \\ R_{4}^{2} = hie \end{array} \right)$$

$$\Rightarrow R_{1}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ hee} \\ R_{1}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ hee} \\ R_{2}^{2} = Iie \right) \\ A_{3}^{2} = hie \left( \begin{array}{c} I - \frac{0.5 hee}{hee} \\ R_{1}^{2} = hie} \\ A_{2}^{2} = Iie} \\ A_{3}^{2} = Iie} \\ A_{4}^{2} = Iie} \\ A_{5}^{2} = Iie} \\ A_{5}^{2} = Iie} \\ A_{6}^{2} = Iie} \\ A_{7}^{2} = Iie} \\ A_{$$

It is the natio of  $V_c$  to  $I_c$  with  $V_s=0$  and  $R_L$  excluded. The simplified cincuit has infinite output impedance because with  $V_s=0$  and external voltage sounce applied at output, it is found that  $I_b=0$  and hence  $I_c=0$ 

$$R_0 = \frac{V_c}{T_c} = \infty \quad \left( \begin{array}{c} \cdot \cdot \cdot & T_c = 0 \end{array} \right)$$

Approximate analysis of CE Amplifier

connent gain AI = -hfe

Input resistance Ri = hie

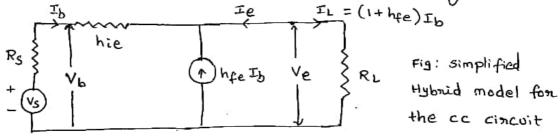
Voltage gain Av = -hfe Ri

hie

output resistance Ro = 00

Analysis of cc Amplifier using the approximate Model:

Figure shows the equivalent circuit of cc Amplifications using the approximate model with the collector grounded, input signal applied between base and ground and load connected between emitter and ground.



i) cunnent gain =-
$$A_{I} = \frac{I_{L}}{I_{b}} = \frac{(1 + hfe)I_{b}}{I_{b}} = (1 + hfe)$$

$$V_b = I_b h_{ie} + (1 + h_{fe}) I_b R_L$$

$$R_i = \frac{V_b}{T_i} = h_{ie} + (1 + h_{fe}) R_L$$

# 3) Voltage gain

$$Av = \frac{Ve}{V_b} = \frac{(1+hfe) I_b R_L}{\left(h_{ie} I_b + (1+hfe) I_b R_L\right)}$$

$$Av = 1 - \frac{hie}{hie + (1+hfe)R_L}$$

$$A_V = 1 - \frac{hie}{Ri}$$
 [" Ri = hie + (1+hfe)RL]

short circuit corrent = 
$$(1 + hfe)Ib = (1 + hfe)Vs$$
  
in output terminals  $= (1 + hfe)Ib = (1 + hfe)Vs$   
 $= (1 + hfe)Ib = (1 + hfe)Vs$ 

open cincuit voltage = Vs bln output terminals

$$\therefore \quad \forall_0 = \frac{1 + hfe}{Rs + hie} \implies Ro = \frac{hie + Rs}{1 + hfe}$$

output impedance including RL ie Ro = Roll RL

Analysis of CB Amplifier using the approximate model

Figure shows the equivalent cincuit of CB amplifien using the approximate model, with the base grounded, input signal is applied between emitter and base and load connected between Collector and base

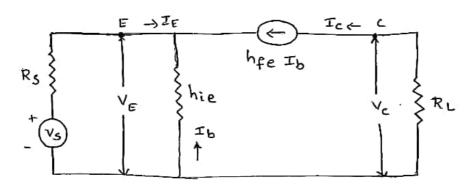


Fig: Simplified Hybrid model for the CB circuit

# 1) corrent gain!

From the figure above 
$$A_{I} = \frac{-I_{C}}{I_{e}} = \frac{-h_{fe} I_{b}}{I_{e}}$$

$$I_{e} = -(I_{b} + I_{c})$$

$$I_{e} = -(I_{b} + h_{fe} I_{b}) = -(I + h_{fe}) I_{b}$$

$$A_{I} = \frac{-h_{fe} I_{b}}{-(I + h_{fe}) I_{b}} = \frac{h_{fe}}{I + h_{fe}} = -h_{fb}$$

# 2) Input Resistance:

From figure 
$$Ve = -Ibhie$$
,  $Ie = -(1+hfe)Ib$ 

$$R_1 = \frac{hie}{1+hfe} = hib$$

3) voitage gain:

$$A_V = \frac{V_c}{V_c}$$

$$V_c = -I_c R_L = -h_f e I_b R_L$$
 $V_c = -I_b h_i e$ 

$$A_V = \frac{h_f e R_L}{h_i e}$$

#### output Impedance

$$R_0 = \frac{V_C}{T_C}$$
 with  $V_S = 0$ ,  $R_L = \infty$ 

with  $V_s=0$ ,  $I_e=0$  and  $I_b=0$  hence  $I_c=0$ 

$$\therefore R_0 = \frac{V_C}{o} = \infty$$

Approximate Analysis of CB Amplifier

- 1) corrent gain AI = hfe = -hfb
- 2) Input Resistance Ri = hie = hib
- 3) Voltage gain Av = her RL
- 4) output resistance Ro = 00

Approximate Analysis of CC Amplifier

- i) corrent gain AI = (1+ hfe)
- 2) Input nesistance Ri = hie + (1 + hfe) RL
- 3) voitage gain  $Av = 1 \frac{hie}{Ri}$
- 4) output Resistance Ro = hie + Rs

  1+ hee